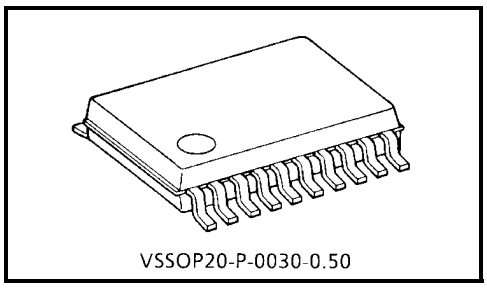
TOSHIBA CMOS Didital Integrated Circuit Silicon Monolithic

TC7MET240AFK, TC7MET244AFK

Octal Bus Buffer

TC7MET240AFK Inverted, 3-State Outputs

TC7MET244AFK Non-Inverted, 3-State Outputs



Weight: 0.03 g (typ.)

The TC7MET240AFK and 244AFK are advanced high speed CMOS octal bus buffers fabricated with silicon gate C^2MOS technology. They achieve the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

The TC7MET240AFK is an inverting 3-state buffer having two active-low output enables. TC7MET244AFK is a non-inverting 3-state buffer, and has two active-low output enables.

These devices are designed to be used with 3-state memory address drivers, etc.

The input voltage are compatible with TTL output voltage.

These devices may be used as a level converter for interfacing 3.3 V to 5 V system.

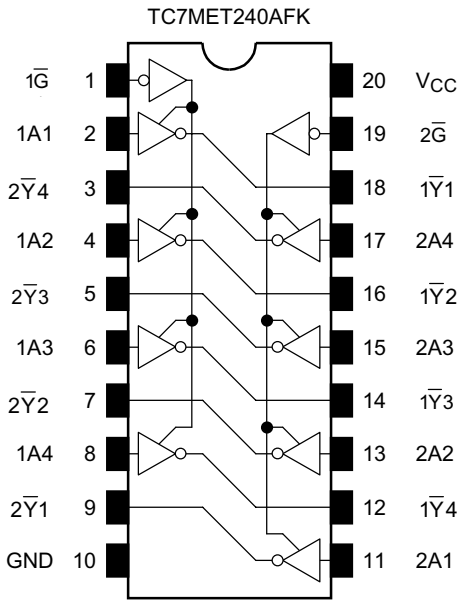
Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output (*) pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

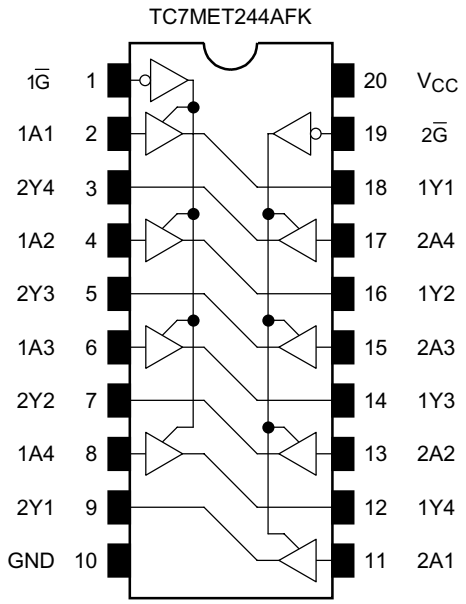
*: output in off-state

Features

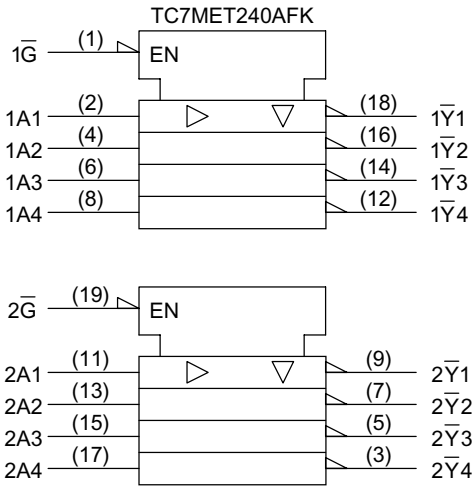
- High speed: t_{pd} = 5.6 ns (typ.) (V_{CC} = 5 V)
- Low power dissipation: I_{CC} = 4 μA (max) (Ta = 25°C)
- Compatible with TTL outputs: V_{IL} = 0.8 V (max)
  V_{IH} = 2.0 V (min)
- Power down protection is provided on all inputs and outputs.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Low noise: V_{OLP} = 1.0 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 240/244 type.

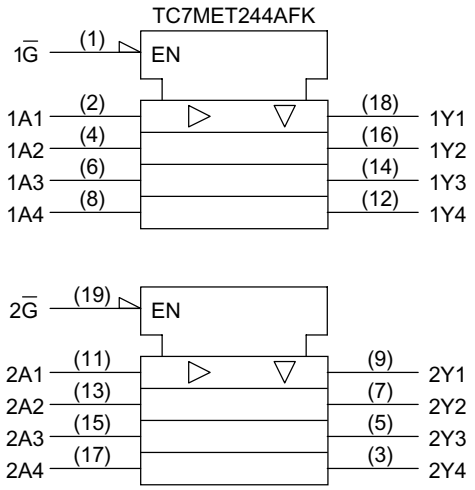
Pin Assignment (top view)





IEC Logic Symbol





Truth Table

Inputs		Outputs	
$\overline{G}$	A_n	Y_n	$\overline{Y}_n$
L	L	L	H
L	H	H	L
H	X	Z	Z

X: Don't care

Z: High impedance

Y_n: TC7MET244AFK

$\overline{Y}_n$: TC7MET240AFK

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	−0.5~7.0	V
DC input voltage	V_{IN}	−0.5~7.0	V
DC output voltage	V_{OUT}	−0.5~7.0 (Note1)	V
		−0.5~V_{CC} + 0.5 (Note2)	
Input diode current	I_{IK}	−20	mA
Output diode current	I_{OK}	±20 (Note3)	mA
DC output current	I_{OUT}	±25	mA
DC V_{CC}/ground current	I_{CC}	±75	mA
Power dissipation	P_D	180	mW
Storage temperature	T_{stg}	−65~150	°C

Note1: Output in off-state

Note2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note3: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	4.5~5.5	V
Input voltage	V_{IN}	0~5.5	V
Output voltage	V_{OUT}	0~5.5 (Note4)	V
		0~V_{CC} (Note5)	
Operating temperature	T_{opr}	−40~85	°C
Input rise and fall time	dt/dv	0~20	ns/V

Note4: Output in off-state

Note5: High or low state

Electrical Characteristics

DC Characteristics

Characteristics		Symbol	Test Condition		V_{CC} (V)	Ta = 25°C Min	Ta = 25°C Typ.	Ta = 25°C Max	Ta = −40~85°C Min	Ta = −40~85°C Max	Unit
Input voltage	High level	V_{IH}	—		4.5~5.5	2.0	—	—	2.0	—	V
	Low level	V_{IL}	—		4.5~5.5	—	—	0.8	—	0.8	
Output voltage	High level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −50 μA	4.5	4.4	4.5	—	4.4	—	V
				I_{OH} = −8 mA	4.5	3.94	—	—	3.80	—	
	Low level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 50 μA	4.5	—	0	0.1	—	0.1	
				I_{OL} = 8 mA	4.5	—	—	0.36	—	0.44	
3-state output off-state current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = V_{CC} or GND		5.5	—	—	±0.25	—	±2.50	μA
Input leakage current		I_N	V_{IN} = 5.5 V or GND		0~5.5	—	—	±0.1	—	±1.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		5.5	—	—	4.0	—	40.0	μA
		I_{CCT}	Per input: V_{IN} = 3.4 V Other input: V_{CC} or GND		5.5	—	—	1.35	—	1.50	mA
Output leakage current		I_{OPD}	V_{OUT} = 5.5 V		0	—	—	0.5	—	5.0	μA

AC Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	V_{CC} (V)	C_L (pF)	Ta = 25°C Min	Ta = 25°C Typ.	Ta = 25°C Max	Ta = −40~85°C Min	Ta = −40~85°C Max	Unit
Propagation delay time (TC7MET240AFK)	t_{pLH} t_{pHL}	—	5.0 ± 0.5	15	—	5.6	7.8	1.0	9.0	ns
				50	—	6.1	8.8	1.0	10.0	
Propagation delay time (TC7MET244AFK)	t_{pLH} t_{pHL}	—	5.0 ± 0.5	15	—	5.4	7.4	1.0	8.5	ns
				50	—	5.9	8.4	1.0	9.5	
3-state output enable time	t_{pZL} t_{pZH}	R_L = 1 kΩ	5.0 ± 0.5	15	—	7.7	10.4	1.0	12.0	ns
				50	—	8.2	11.4	1.0	13.0	
3-state output disable time	t_{pLZ} t_{pHZ}	R_L = 1 kΩ	5.0 ± 0.5	50	—	8.8	11.4	1.0	13.0	ns
Output to output skew	t_{osLH} t_{osHL}	(Note6)	5.0 ± 0.5	50	—	—	1.0	—	1.0	ns
Input capacitance	C_{IN}	—			—	4	10	—	10	pF
Output capacitance	C_{OUT}	—			—	9	—	—	—	pF
Power dissipation capacitance (Note7)	C_{PD}	TC7MET240AFK			—	19	—	—	—	pF
		TC7MET244AFK			—	18	—	—	—	

Note6: Parameter guaranteed by design.
$t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$

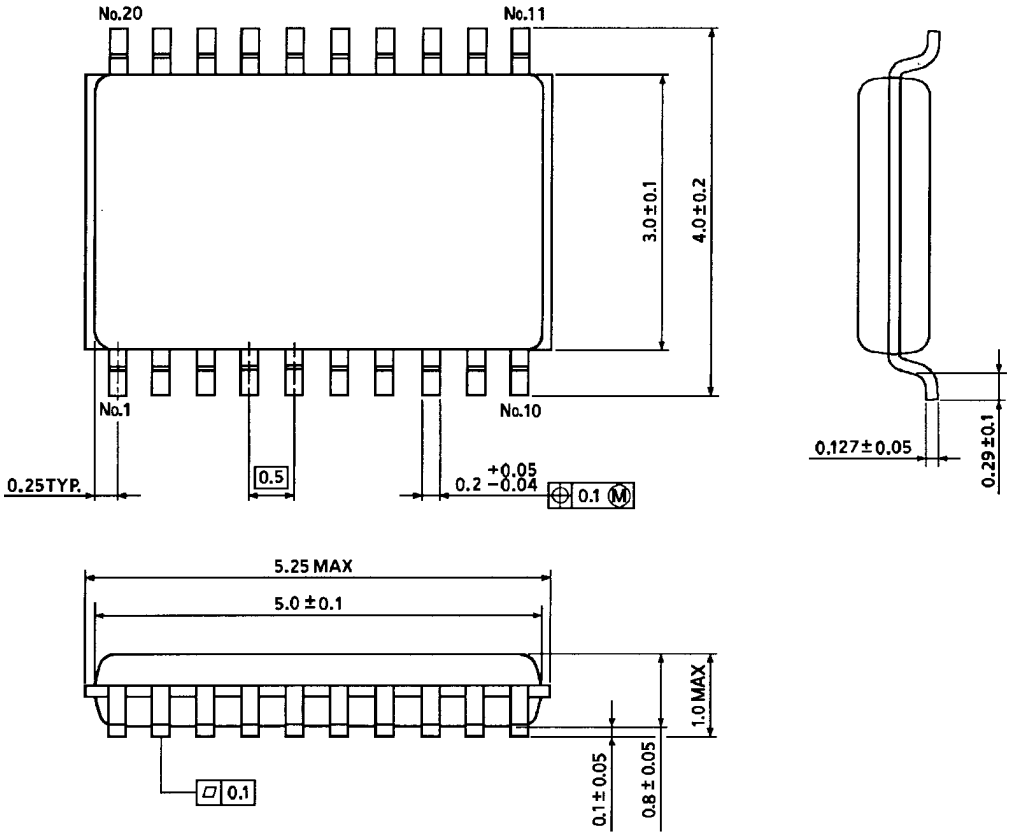
Note7: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation:
$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per bit)

Noise Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	Ta = 25°C		Unit
			V_{CC} (V)	Typ.	Limit	
Quiet output maximum dynamic V_{OL}	V_{OLP}	C_L = 50 pF	5.0	0.8	1.0	V
Quiet output minimum dynamic V_{OL}	V_{OLV}	C_L = 50 pF	5.0	−0.8	−1.0	V
Minimum high level dynamic input voltage V_{IH}	V_{IHD}	C_L = 50 pF	5.0	—	2.0	V
Maximum high level dynamic input voltage V_{IL}	V_{ILD}	C_L = 50 pF	5.0	—	0.8	V

Package Dimensions

VSSOP20-P-0030-0.50 Unit : mm



Weight: 0.03 g (typ.)